

FEATURES

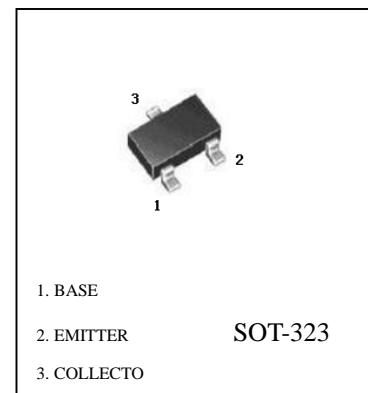
Epitaxial planar die construction.
 Complementary PNP type available(MMST5401).
 Also available in lead free version.

Marking:K4N

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current -Continuous	I _C	600	mA
Collector Power Dissipation	P _C	300	mW
Thermal resistance junction to ambient	R _{JA}	625	°C/W
Storage Temperature	T _{Stg}	-55 to +150	°C

MMST5551 (NPN)



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Umit
Collector-base breakdown voltage	V _{CBO}	I _C =100μA,I _E =0	180		
Collector-emitter breakdown voltage	V _{CEO}	I _C =0.1mA,I _B =0	160		
Emitter-base breakdown voltage	V _{EBO}	I _E =10μA,I _C =0	6		
Collector cut-off current	I _{CBO}	I _E = 0; V _{CB} = 120V	-	50	nA
Emitter cut-off current	I _{EBO}	I _C = 0; V _{EB} = 4V	-	50	nA
DC current gain	h _{FE}	V _{CE} = 5V; I _C = 1mA V _{CE} = 5V;I _C = 10mA V _{CE} = 5V;I _C = 50 Ma	80 80 30	- 250 -	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 50 mA; I _B = 5 mA I _C = 10 mA; I _B = 1 mA	-	0.2 0.15	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 50 mA; I _B = 5 mA I _C = 10 mA; I _B = 1 mA	-	1 1	V
Transition frequency	f _T	I _C = 10mA; V _{CE} = 10V; f = 100MHz	80	-	MHz

MMST5551 Typical Characteristics

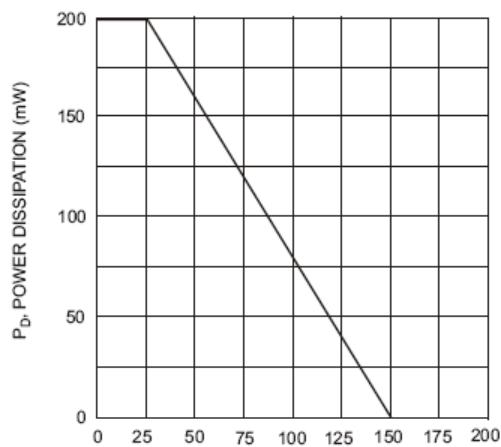


Fig. 1, Max Power Dissipation vs.
Ambient Temperature

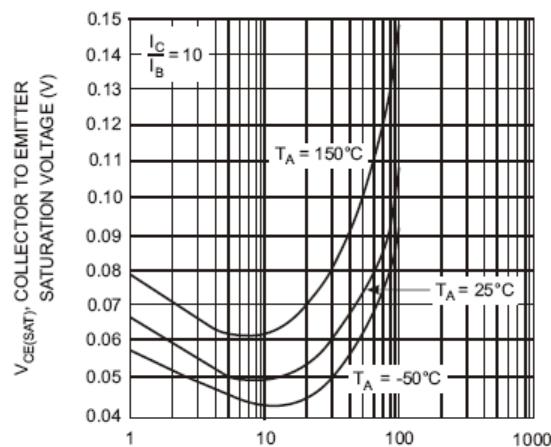


Fig. 2, Collector Emitter Saturation Voltage
vs. Collector Current

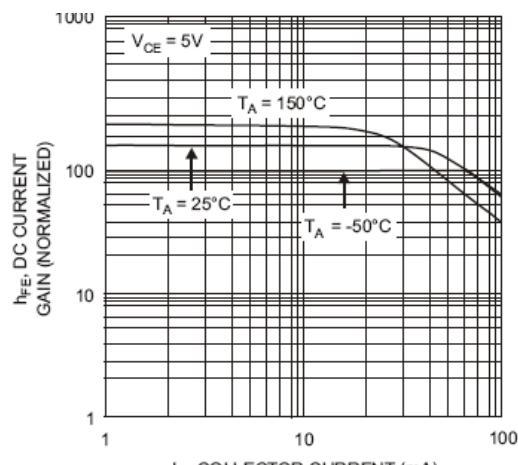


Fig. 3, DC Current Gain vs.
Collector Current

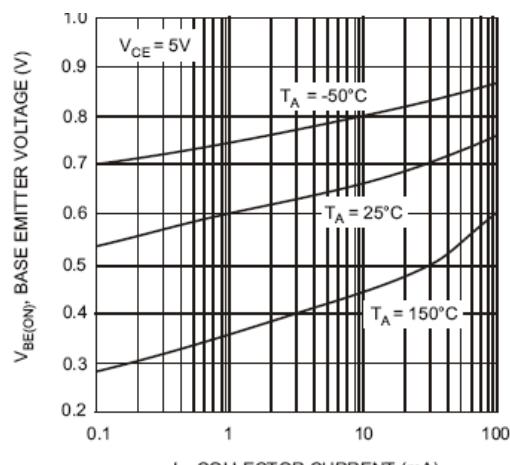


Fig. 4, Base Emitter Voltage
vs. Collector Current

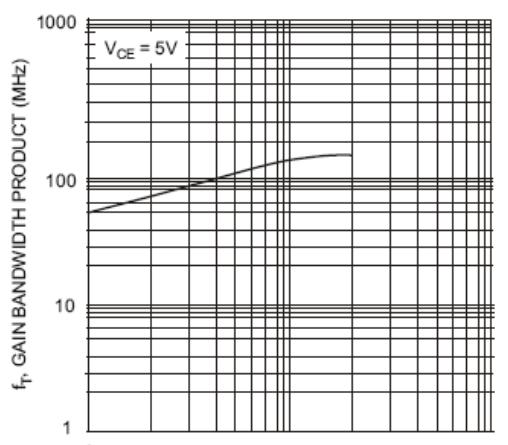


Fig. 5, Gain Bandwidth Product vs.
Collector Current